

Legacy Device: Motorola MC1490

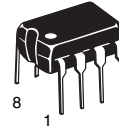
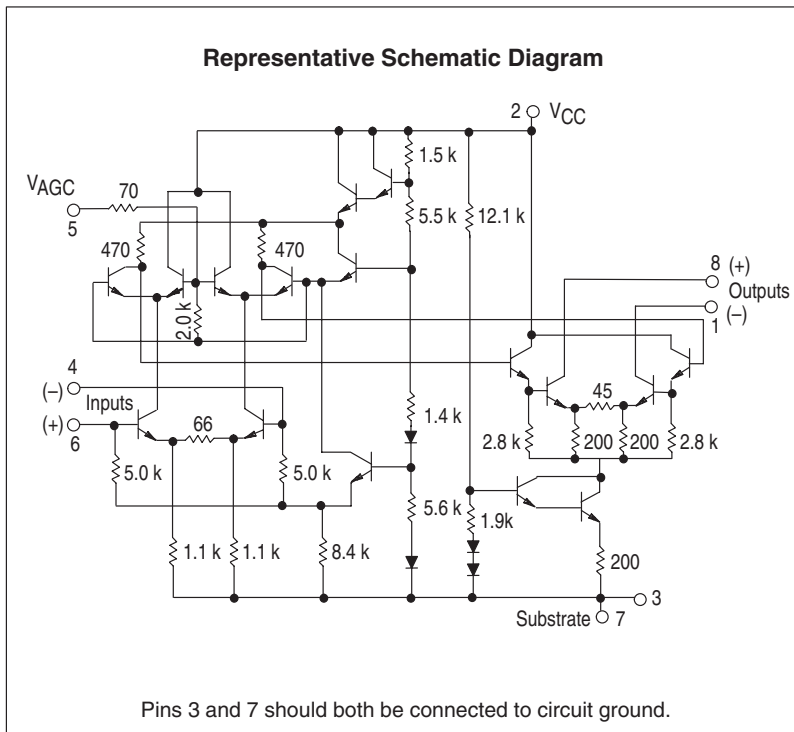
The ML1490 is an integrated circuit featuring wide-range AGC for use in RF/IF amplifiers and audio amplifiers.

- High Power Gain:
  - 50 dB Typ at 10 MHz
  - 45 dB Typ at 60 MHz
  - 35 dB Typ at 100 MHz
- Wide Range AGC: 60 dB Min, DC to 60 MHz
- 6.0 V to 15 V Operation, Single Polarity Supply
- Operating Temperature Range  $T_A = -40^\circ$  to  $+85^\circ\text{C}$

Note: See Similar ML1350 For Possible Option

**MAXIMUM RATINGS** ( $T_A = +25^\circ\text{C}$ , unless otherwise noted.)

Rating	Symbol	Value	Unit
Power Supply Voltage	$V_{CC}$	+18	Vdc
AGC Supply	$V_{AGC}$	$V_{CC}$	Vdc
Input Differential Voltage	$V_{ID}$	5.0	Vdc
Operating Temperature Range	$T_A$	$-40$ to $+85$	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	$-65$ to $+150$	$^\circ\text{C}$
Junction Temperature	$T_J$	+150	$^\circ\text{C}$



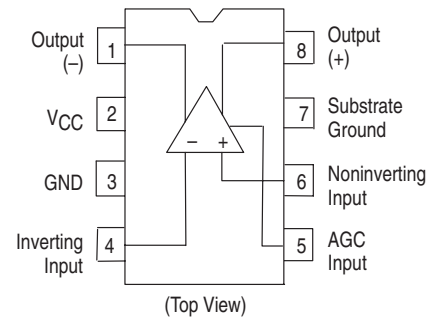
**P DIP 8 = PP**  
PLASTIC PACKAGE  
CASE 626

**CROSS REFERENCE/ORDERING INFORMATION**

PACKAGE	MOTOROLA	LANSDALE
P DIP 8	MC1490P	ML1490PP

Note: Lansdale lead free (Pb) product, as it becomes available, will be identified by a part number prefix change from ML to MLE.

**PIN CONNECTIONS**



**SCATTERING PARAMETERS**

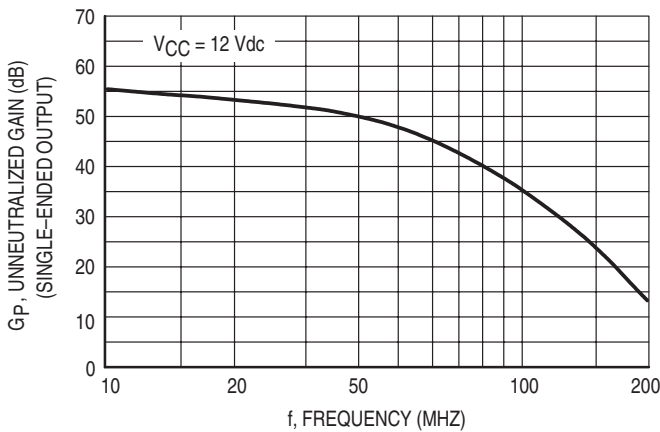
( $V_{CC} = +12$  Vdc,  $T_A = +25^\circ\text{C}$ ,  $Z_0 = 50 \Omega$ )

Parameter	Symbol	f = MHz		Unit
		30	60	
Input Reflection Coefficient	$ S_{11} $ $\theta_{11}$	0.95 -7.3	0.93 -16	- deg
Output Reflection Coefficient	$ S_{22} $ $\theta_{22}$	0.99 -3.0	0.98 -5.5	- deg
Forward Transmission Coefficient	$ S_{21} $ $\theta_{21}$	16.8 128	14.7 64.3	- deg
Reverse Transmission Coefficient	$S_{12}$ $\theta_{12}$	0.00048 84.9	0.00092 79.2	- deg

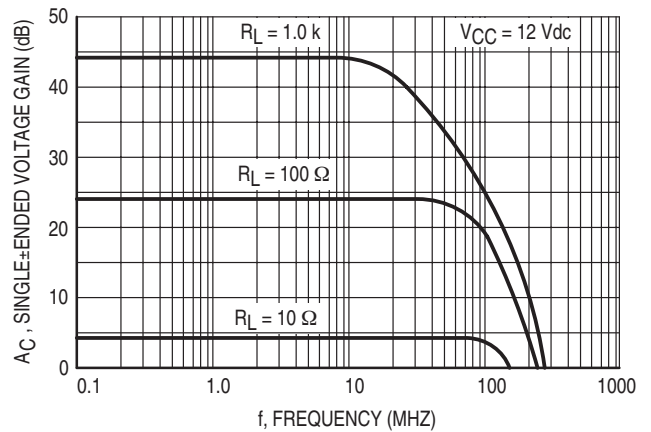
**ELECTRICAL CHARACTERISTICS** ( $V_{CC} = 12\text{ Vdc}$ ,  $f = 60\text{ MHz}$ ,  $BW = 1.0\text{ MHz}$ ,  $T_A = 25\text{[C]}$ )

Characteristic	Figure	Symbol	Min	Typ	Max	Unit
Power Supply Current Drain	–	$I_{CC}$	–	–	17	mA
AGC Range (AGC) 5.0 V Min to 7.0 V Max	19	$M_{AGC}$	–60	–	–	dB
Output Stage Current (Sum of Pins 1 and 8)	–	$I_O$	4.0	–	7.5	mA
Single-Ended Power Gain $R_S = R_L = 50\ \Omega$	19	$G_P$	40	–	–	dB
Noise Figure $R_S = 50\ \text{Ohms}$	19	NF	–	6.0	–	dB
Power Dissipation	–	$P_D$	–	168	204	mW

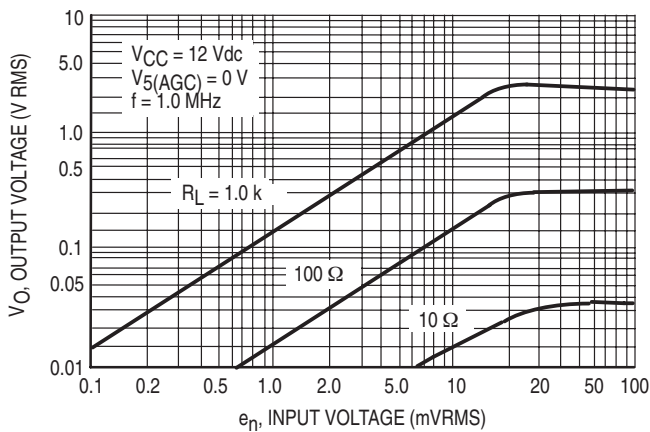
**Figure 1. Unneutralized Power Gain versus Frequency (Tuned Amplifier, See Figure 19)**



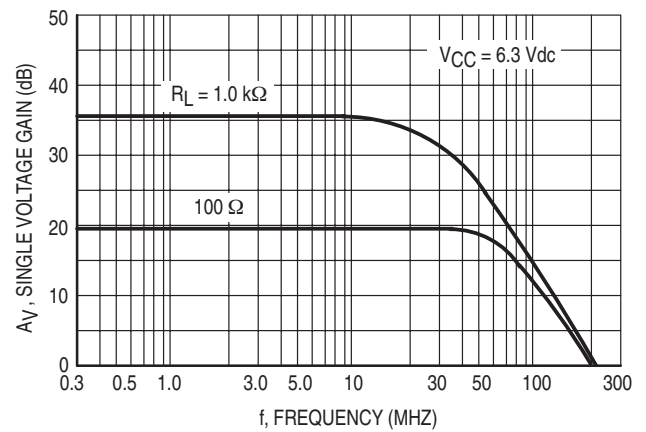
**Figure 2. Voltage Gain versus Frequency (Video Amplifier, See Figure 20)**



**Figure 3. Dynamic Range: Output Voltage versus Input Voltage (Video Amplifier, See Figure 20)**

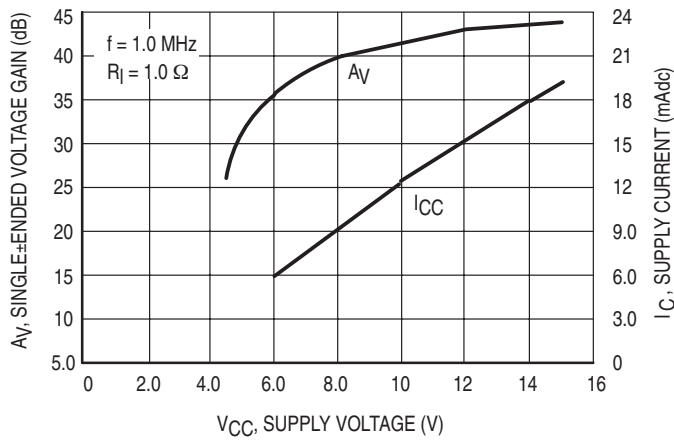


**Figure 4. Voltage Gain versus Frequency (Video Amplifier, See Figure 20)**

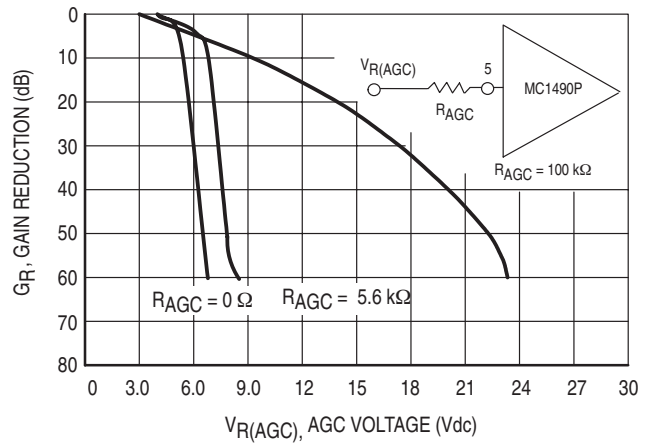


Legacy Applications Information

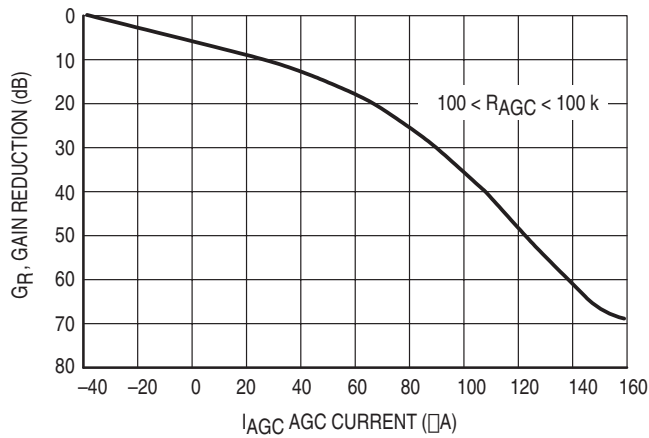
**Figure 5. Voltage Gain and Supply Current versus Supply Voltage (Video Amplifier, See Figure 20)**



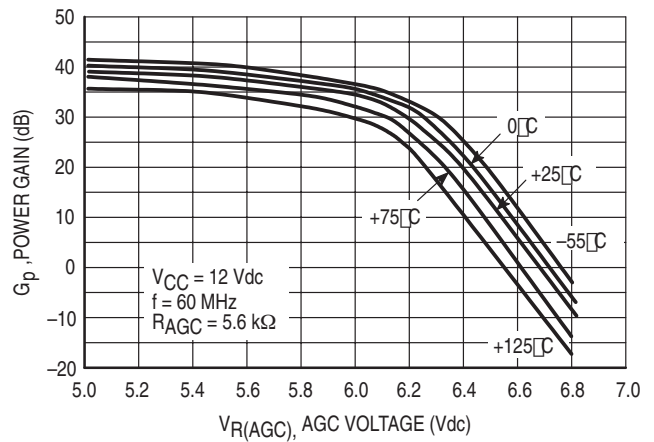
**Figure 6. Typical Gain Reduction versus AGC Voltage**



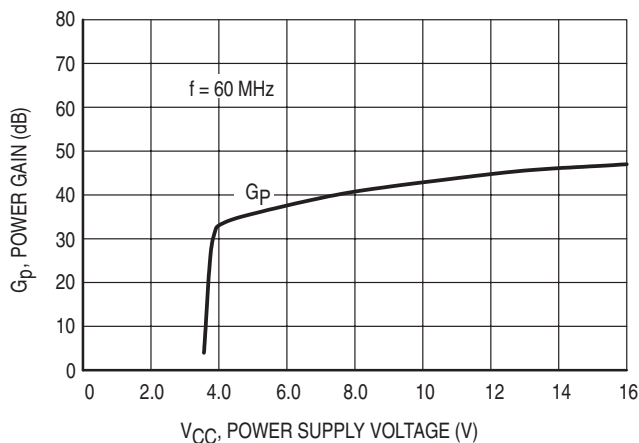
**Figure 7. Typical Gain Reduction versus AGC Current**



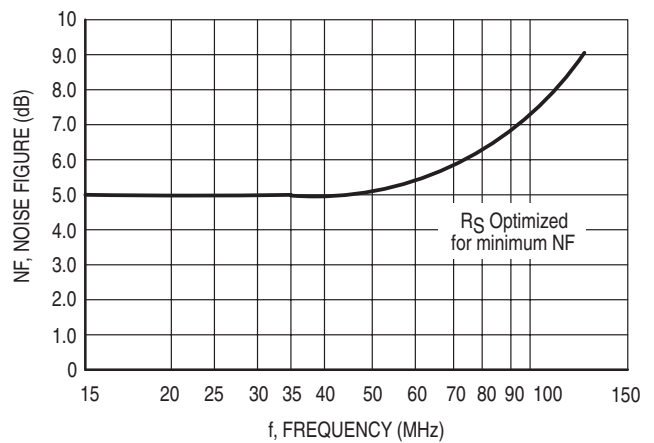
**Figure 8. Fixed Tuned Power Gain Reduction versus Temperature (See Test Circuit, Figure 19)**



**Figure 9. Power Gain versus Supply Voltage (See Test Circuit, Figure 19)**

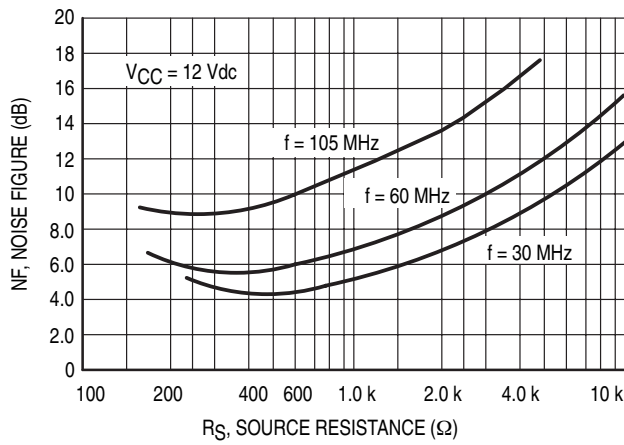


**Figure 10. Noise Figure versus Frequency**

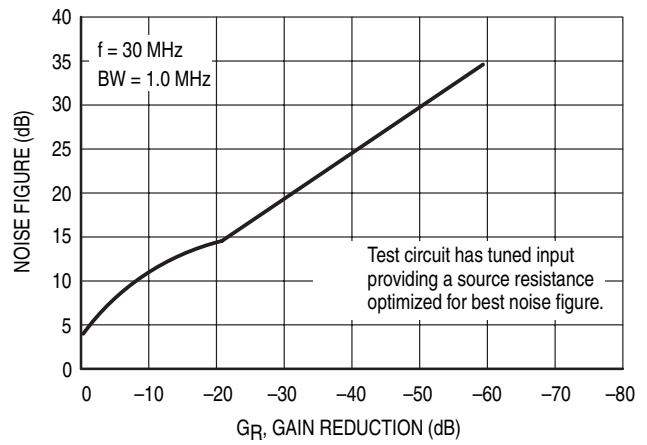


Legacy Applications Information

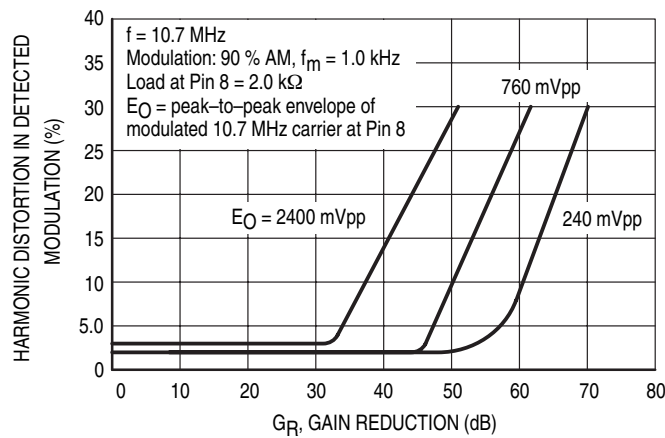
**Figure 11. Noise Figure versus Source Resistance**



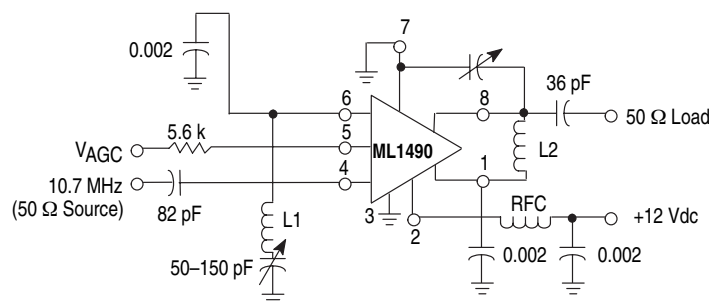
**Figure 12. Noise Figure versus AGC Gain Reduction**



**Figure 13. Harmonic Distortion versus AGC Gain Reduction for AM Carrier (For Test Circuit, See Figure 14)**



**Figure 14. 10.7 MHz Amplifier Gain 55 dB, BW 100 kHz**



L1 = 24 turns, #22 AWG wire on a T12-44 micro metal Toroid core (-124 pF)

L2 = 20 turns, #22 AWG wire on a T12-44 micro metal Toroid core (-100 pF)

Legacy Applications Information

Figure 15.  $S_{11}$  and  $S_{22}$ , Input and Output Reflection Coefficient

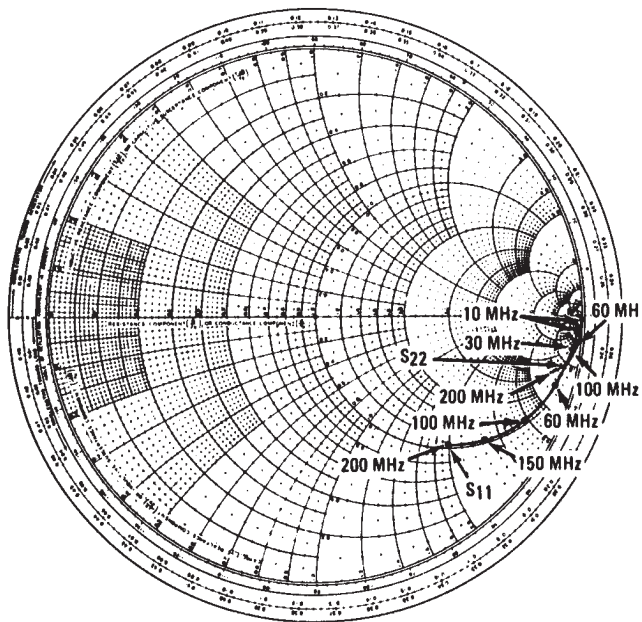


Figure 16.  $S_{11}$  and  $S_{22}$ , Input and Output Reflection Coefficient

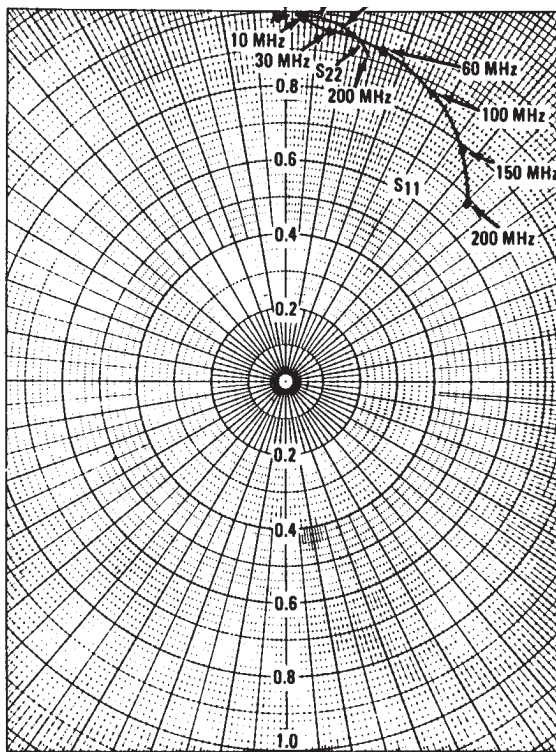


Figure 17.  $S_{21}$ , Forward Transmission Coefficient (Gain)

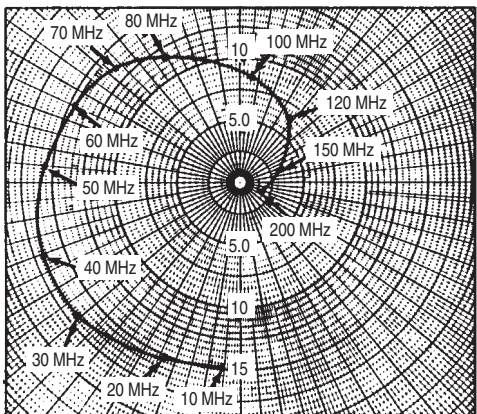
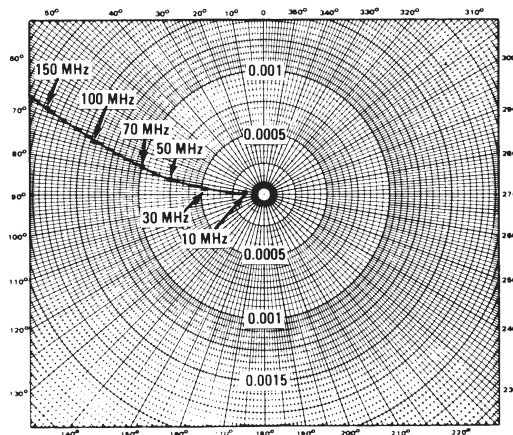
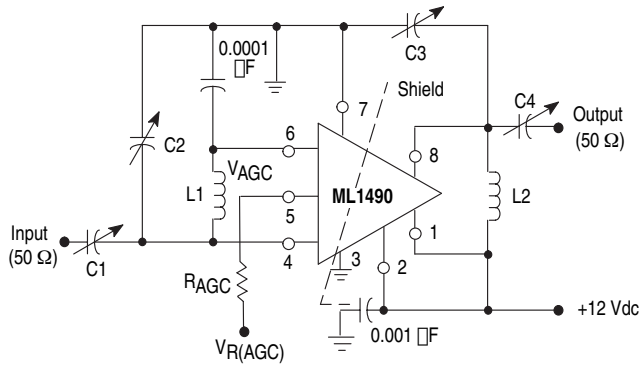


Figure 18.  $S_{12}$ , Reverse Transmission Coefficient (Feedback)



Legacy Applications Information

Figure 19. 60 MHz Power Gain Test Circuit



L1 = 7 turns, #20 AWG wire, 5/16" Dia., 5/8" long  
 L2 = 6 turns, #14 AWG wire, 9/16" Dia., 3/4" long  
 C1, C2, C3 = (1-30) pF  
 C4 = (1-10) pF

Figure 20. Video Amplifier

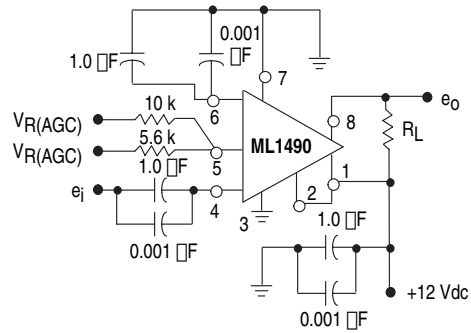
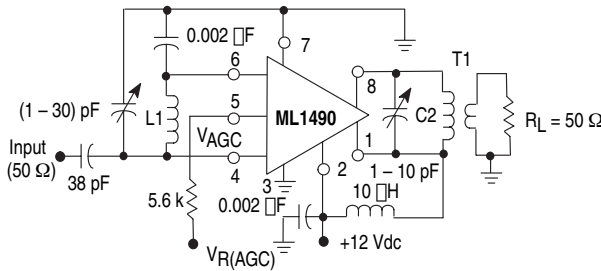
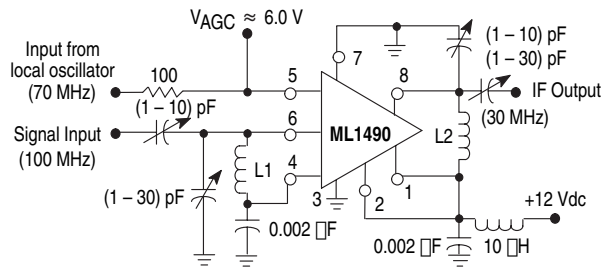


Figure 21. 30 MHz Amplifier  
 (Power Gain = 50 dB, BW 1.0 MHz)



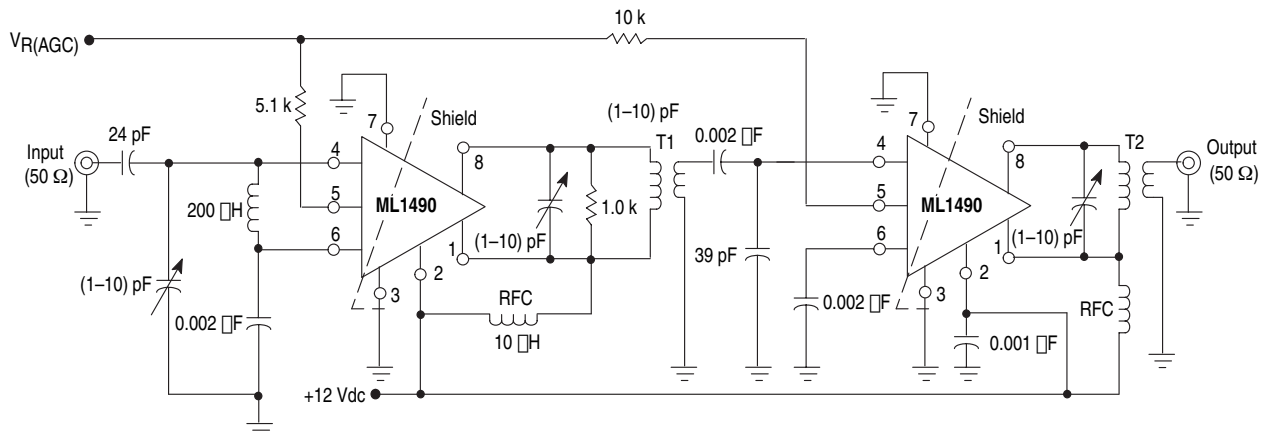
L1 = 12 turns, #22 AWG wire on a Toroid core,  
 (T37-6 micro metal or equiv).  
 T1: Primary = 17 turns, #20 AWG wire on a Toroid core, (T44-6).  
 Secondary = 2 turns, #20 AWG wire.

Figure 22. 100 MHz Mixer



L1 = 5 turns, #16 AWG wire, 1/4", ID Dia., 5/8" long  
 L2 = 16 turns, #20 AWG wire on a Toroid core, (T44-6).

Figure 23. Two-Stage 60 MHz IF Amplifier (Power Gain 80 dB, BW 1.5 MHz)



T1: Primary Winding = 15 turns, #22 AWG wire, 1/4" ID Air Core  
 Secondary Winding = 4 turns, #22 AWG wire,  
 Coefficient of Coupling ≈ 1.0

T2: Primary Winding = 10 turns, #22 AWG wire, 1/4" ID Air Core  
 Secondary Winding = 2 turns, #22 AWG wire,  
 Coefficient of Coupling ≈ 1.0

**DESCRIPTION OF SPEECH COMPRESSOR**

The amplifier drives the base of a PNP transistor operating common-emitter with a voltage gain of approximately 20. The control R1 varies the quiescent Q point of this transistor so that varying amounts of signal exceed the level  $V_T$ . Diode D1 rectifies the positive peaks of Q1's output only when these peaks are greater than  $V_T \approx 7.0$  V. The resulting output is filtered by  $C_X$ ,  $R_X$ .

$R_X$  controls the charging time constant or attack time.  $C_X$  is involved in both charge and discharge. R2 (the 150 k $\Omega$  and input resistance of the emitter-follower Q2) controls the decay time. Making the decay long and attack short is accomplished by making  $R_X$  small and R2 large. (A Darlington emitter-follower may be needed if extremely slow decay times are required.)

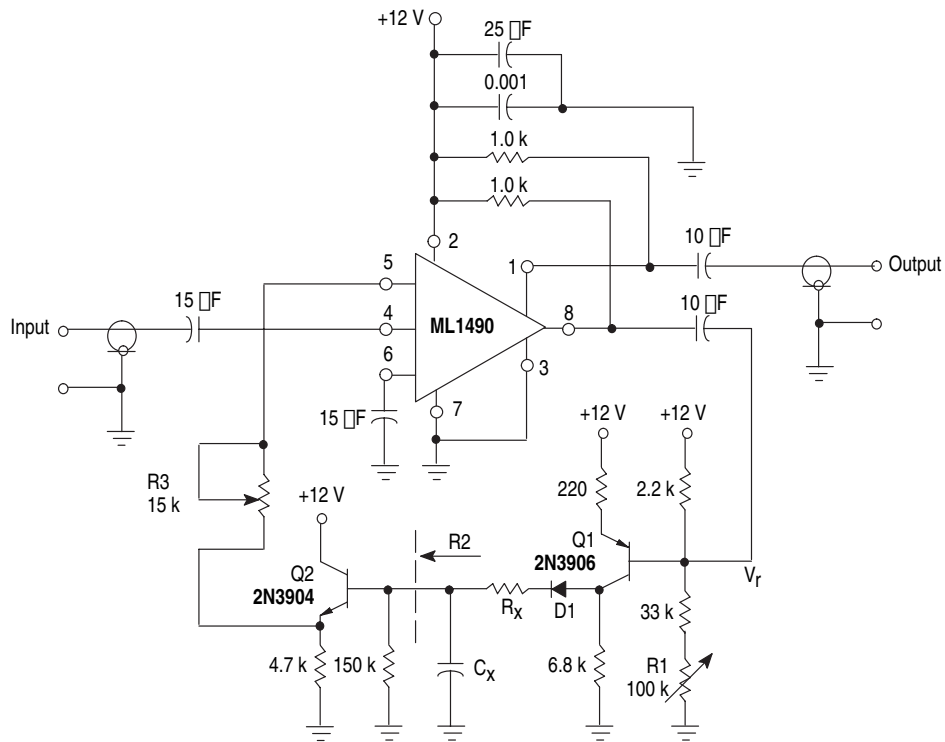
The emitter-follower Q2 drives the AGC Pin 5 of the ML1490PP and reduces the gain. R3 controls the slope of signal compression.

**Table 1. Distortion versus Frequency**

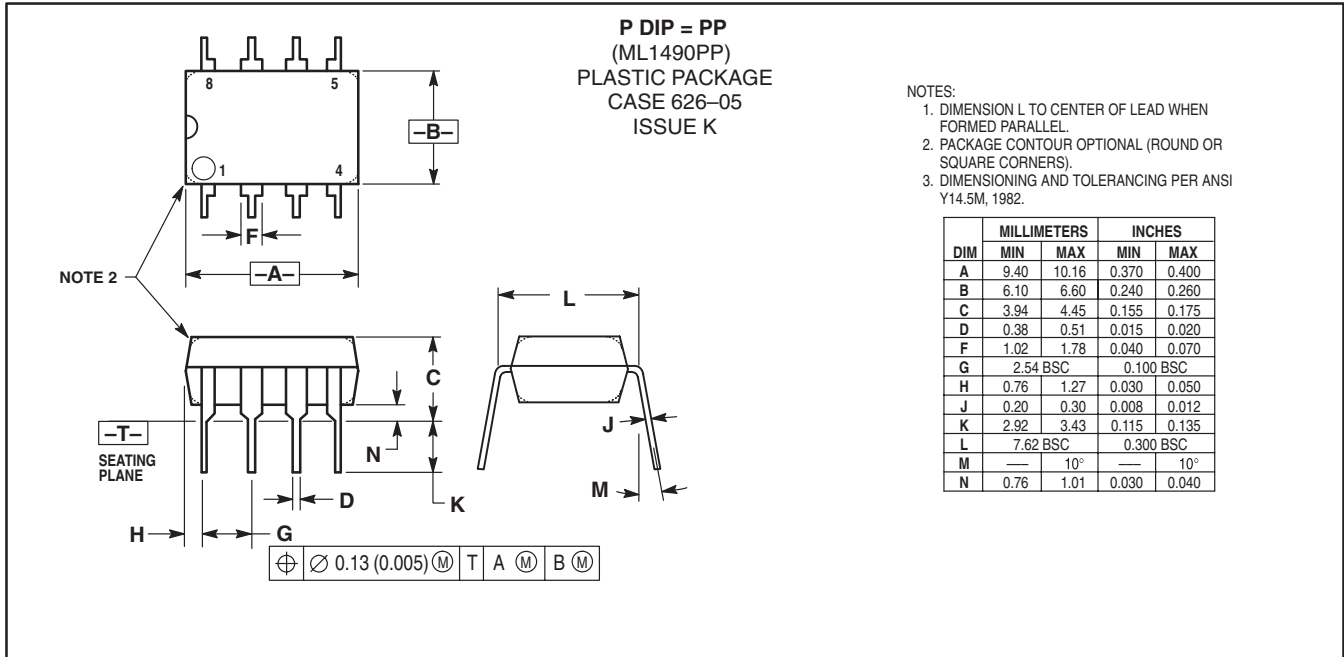
Frequency	Distortion		Distortion	
	10 mV $e_i$	100 mV $e_i$	10 mV $e_i$	100 mV $e_i$
100 Hz	3.5%	12%	15%	27%
300 Hz	2%	10%	6%	20%
1.0 kHz	1.5%	8%	3%	9%
10 kHz	1.5%	8%	1%	3%
100 kHz	1.5%	8%	1%	3%
	Notes 1 and 2		Notes 3 and 4	

- Notes:** (1) Decay = 300 ms  
Attack = 20 ms  
(2)  $C_X = 7.5 \mu\text{F}$   
 $R_X = 0$  (Short)
- (3) Decay = 20 ms  
Attack = 3.0 ms  
(4)  $C_X = 0.68 \mu\text{F}$   
 $R_X = 1.5 \text{ k}\Omega$

**Figure 24. Speech Compressor**



OUTLINE DIMENSIONS



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